

## NEGATIVE PHOTORESISTIVE RESIN COMPOSITION

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### Abstract of JP2002040659

**PROBLEM TO BE SOLVED:** To provide a photosensitive resin composition which can be developed with an alkali aqueous solution, has high sensitivity and from which a pattern thin film having various superior characteristics, such as insulating property, flatness, heat resistance, solvent resistance or the like can be easily formed, and moreover, to provide a photosensitive resin composition from which a pattern thin film excellent in the above characteristics as well as low dielectric characteristics can be easily formed, and to provide a method for processing the composition.

**SOLUTION:** The negative photosensitive resin composition contains tetrafluoroethylene, a fluorine-containing copolymer obtained by copolymerization of monomers having carboxyl groups and monomers copolymerizable with these monomers, a melamine-crosslinking agent and a photoacid-generating agent. The negative photosensitive resin composition is subjected to processes of application, exposure, alkali development, and then rinsing by ultrahigh pressure microjet.

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